

MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE

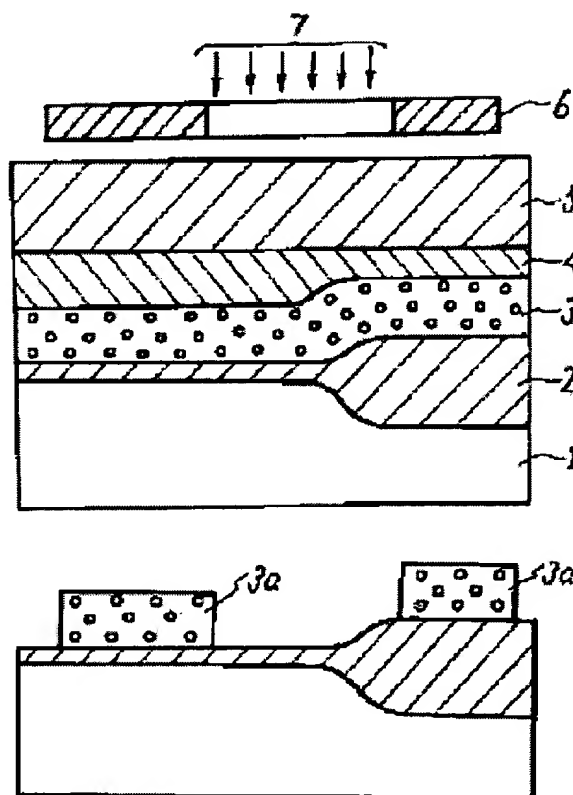
Patent number: JP8153704
Publication date: 1996-06-11
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Classification:
- international: H01L21/3065; H01L21/027; H01L27/108; H01L21/8242
- european:
Application number: JP19940292988 19941128
Priority number(s): JP19940292988 19941128

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Abstract of JP8153704

PURPOSE: To prevent etching in a horizontal direction with a photo-resist and organic ARC film by forming a conductive film and an organic ARC film on an insulation film provided on a substrate along with a step part and, using photo-resist as a mask, etching the organic ARC film with N₂ gas plasma.

CONSTITUTION: First, a silicon substrate 1, a LOCOS oxide film 2, an insulation film and a polysilicon film 3 are formed by a CVD method, and further an organic ARC 4 is formed by rotational coating. Then, after coating with a photo-resist 5, the resist is patterned by a photomask 6 and exposed light 7, and further, the organic ARC film is etched. Then, using the mask and organic ARC film as masks, RIE etching is performed on the polysilicon film 3 of conductive film by Cl₂ gas plasma, and then the photo-resist mask and the organic ARC film 4 are incinerated for removal, thus, a wiring layer 3 with a base material step but no pattern tapering caused by etching is formed.



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